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Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

#### Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine, Security; SEC
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (1)
SATA	-
USB	USB 1.x (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	740-LBGA
Supplier Device Package	740-TBGA (37.5x37.5)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360eczuaddh">https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8360eczuaddh</a>

## 6.1 DDR and DDR2 SDRAM DC Electrical Characteristics

This table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the device when  $GV_{DD}(\text{typ}) = 1.8 \text{ V}$ .

**Table 14. DDR2 SDRAM DC Electrical Characteristics for  $GV_{DD}(\text{typ}) = 1.8 \text{ V}$**

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	$GV_{DD}$	1.71	1.89	V	1
I/O reference voltage	$MV_{REF}$	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	$V_{TT}$	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3
Input high voltage	$V_{IH}$	$MV_{REF} + 0.125$	$GV_{DD} + 0.3$	V	—
Input low voltage	$V_{IL}$	-0.3	$MV_{REF} - 0.125$	V	—
Output leakage current	$I_{OZ}$	—	$\pm 10$	$\mu\text{A}$	4
Output high current ( $V_{OUT} = 1.420 \text{ V}$ )	$I_{OH}$	-13.4	—	mA	—
Output low current ( $V_{OUT} = 0.280 \text{ V}$ )	$I_{OL}$	13.4	—	mA	—
$MV_{REF}$ input leakage current	$I_{VREF}$	—	$\pm 10$	$\mu\text{A}$	—
Input current ( $0 \text{ V} \leq V_{IN} \leq OV_{DD}$ )	$I_{IN}$	—	$\pm 10$	$\mu\text{A}$	—

**Notes:**

- $GV_{DD}$  is expected to be within 50 mV of the DRAM  $GV_{DD}$  at all times.
- $MV_{REF}$  is expected to equal  $0.5 \times GV_{DD}$ , and to track  $GV_{DD}$  DC variations as measured at the receiver. Peak-to-peak noise on  $MV_{REF}$  cannot exceed  $\pm 2\%$  of the DC value.
- $V_{TT}$  is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal  $MV_{REF}$ . This rail should track variations in the DC level of  $MV_{REF}$ .
- Output leakage is measured with all outputs disabled,  $0 \text{ V} \leq V_{OUT} \leq GV_{DD}$ .

This table provides the DDR2 capacitance when  $GV_{DD}(\text{typ}) = 1.8 \text{ V}$ .

**Table 15. DDR2 SDRAM Capacitance for  $GV_{DD}(\text{typ})=1.8 \text{ V}$**

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, $\overline{DQS}$	$C_{IO}$	6	8	pF	1
Delta input/output capacitance: DQ, DQS, $\overline{DQS}$	$C_{DIO}$	—	0.5	pF	1

**Note:**

- This parameter is sampled.  $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$ ,  $f = 1 \text{ MHz}$ ,  $T_A = 25^\circ\text{C}$ ,  $V_{OUT} = GV_{DD}/2$ ,  $V_{OUT}$  (peak-to-peak) = 0.2 V.

This table provides the recommended operating conditions for the DDR SDRAM component(s) of the device when  $GV_{DD}(\text{typ}) = 2.5 \text{ V}$ .

**Table 16. DDR SDRAM DC Electrical Characteristics for  $GV_{DD}(\text{typ}) = 2.5 \text{ V}$**

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	$GV_{DD}$	2.375	2.625	V	1
I/O reference voltage	$MV_{REF}$	$0.49 \times GV_{DD}$	$0.51 \times GV_{DD}$	V	2
I/O termination voltage	$V_{TT}$	$MV_{REF} - 0.04$	$MV_{REF} + 0.04$	V	3

## 6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 21 and Table 22 provide the output AC timing specifications and measurement conditions for the DDR and DDR2 SDRAM interface.

**Table 21. DDR and DDR2 SDRAM Output AC Timing Specifications for Source Synchronous Mode**

At recommended operating conditions with  $GV_{DD}$  of (1.8 V or 2.5 V)  $\pm$  5%.

Parameter <sup>8</sup>	Symbol <sup>1</sup>	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/ $\overline{MCK[n]}$ crossing)	$t_{MCK}$	6	10	ns	2
Skew between any MCK to ADDR/CMD 333 MHz 266 MHz 200 MHz	$t_{AOSKEW}$	-1.0 -1.1 -1.2	0.2 0.3 0.4	ns	3
ADDR/CMD output setup with respect to MCK 333 MHz 266 MHz 200 MHz	$t_{DDKHAS}$	2.1 2.8 3.5	—	ns	4
ADDR/CMD output hold with respect to MCK 333 MHz 266 MHz—DDR1 266 MHz—DDR2 200 MHz	$t_{DDKHAX}$	2.0 2.7 2.8 3.5	—	ns	4
$\overline{MCS}(n)$ output setup with respect to MCK 333 MHz 266 MHz 200 MHz	$t_{DDKHCS}$	2.1 2.8 3.5	—	ns	4
$\overline{MCS}(n)$ output hold with respect to MCK 333 MHz 266 MHz 200 MHz	$t_{DDKHCSX}$	2.0 2.7 3.5	—	ns	4
MCK to MDQS	$t_{DDKMH}$	-0.8	0.7	ns	5, 9
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	$t_{DDKHDS}$ , $t_{DDKLDS}$	0.7 1.0 1.2	—	ns	6
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	$t_{DDKHDX}$ , $t_{DDKLDX}$	0.7 1.0 1.2	—	ns	6
MDQS preamble start	$t_{DDKHMP}$	$-0.5 \times t_{MCK} - 0.6$	$-0.5 \times t_{MCK} + 0.6$	ns	7

### 8.2.1.1 GMII Transmit AC Timing Specifications

This table provides the GMII transmit AC timing specifications.

**Table 27. GMII Transmit AC Timing Specifications**

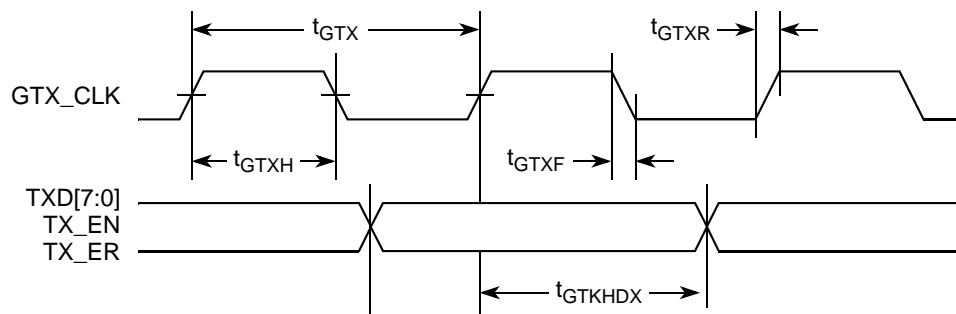
At recommended operating conditions with  $V_{DD}/OV_{DD}$  of  $3.3\text{ V} \pm 10\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit	Notes
GTX_CLK clock period	$t_{GTX}$	—	8.0	—	ns	—
GTX_CLK duty cycle	$t_{GTXH}/t_{GTX}$	40	—	60	%	—
GTX_CLK to GMII data TXD[7:0], TX_ER, TX_EN delay	$t_{GTKHDX}$ $t_{GTKHDV}$	0.5 —	—	— 5.0	ns	3
GTX_CLK clock rise time, (20% to 80%)	$t_{GTXR}$	—	—	1.0	ns	—
GTX_CLK clock fall time, (80% to 20%)	$t_{GTXF}$	—	—	1.0	ns	—
GTX_CLK125 clock period	$t_{G125}$	—	8.0	—	ns	2
GTX_CLK125 reference clock duty cycle measured at $V_{DD}/2$	$t_{G125H}/t_{G125}$	45	—	55	%	2

**Notes:**

1. The symbols used for timing specifications follow the pattern  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$  for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{GTKHDV}$  symbolizes GMII transmit timing (GT) with respect to the  $t_{GTX}$  clock reference (K) going to the high state (H) relative to the time date input signals (D) reaching the valid state (V) to state or setup time. Also,  $t_{GTKHDX}$  symbolizes GMII transmit timing (GT) with respect to the  $t_{GTX}$  clock reference (K) going to the high state (H) relative to the time date input signals (D) going invalid (X) or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of  $t_{GTX}$  represents the GMII(G) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. This symbol is used to represent the external GTX\_CLK125 signal and does not follow the original symbol naming convention.
3. In rev. 2.0 silicon, due to errata,  $t_{GTKHDX}$  minimum and  $t_{GTKHDV}$  maximum are not supported when the GTX\_CLK is selected. Refer to Errata *QE\_ENET18* in *Chip Errata for the MPC8360E, Rev. 1*.

This figure shows the GMII transmit AC timing diagram.



**Figure 10. GMII Transmit AC Timing Diagram**

## 8.2.2 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

### 8.2.2.1 MII Transmit AC Timing Specifications

This table provides the MII transmit AC timing specifications.

**Table 29. MII Transmit AC Timing Specifications**

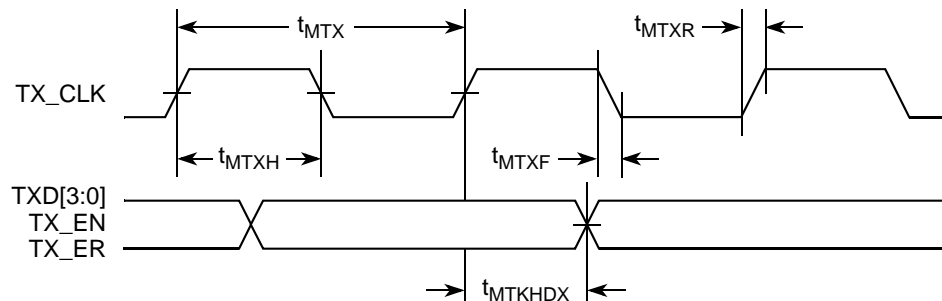
At recommended operating conditions with  $V_{DD}/OV_{DD}$  of  $3.3\text{ V} \pm 10\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit
TX_CLK clock period 10 Mbps	$t_{MTX}$	—	400	—	ns
TX_CLK clock period 100 Mbps	$t_{MTX}$	—	40	—	ns
TX_CLK duty cycle	$t_{MTXH}/t_{MTX}$	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	$t_{MTKHDX}$ $t_{MTKHDXV}$	1 —	5	— 15	ns
TX_CLK data clock rise time, (20% to 80%)	$t_{MTXR}$	1.0	—	4.0	ns
TX_CLK data clock fall time, (80% to 20%)	$t_{MTXF}$	1.0	—	4.0	ns

**Note:**

- The symbols used for timing specifications follow the pattern of  $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$  for inputs and  $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$  for outputs. For example,  $t_{MTKHDX}$  symbolizes MII transmit timing (MT) for the time  $t_{MTX}$  clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of  $t_{MTX}$  represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the MII transmit AC timing diagram.



**Figure 12. MII Transmit AC Timing Diagram**

## 8.2.3 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

### 8.2.3.1 RMII Transmit AC Timing Specifications

This table provides the RMII transmit AC timing specifications.

**Table 31. RMII Transmit AC Timing Specifications**

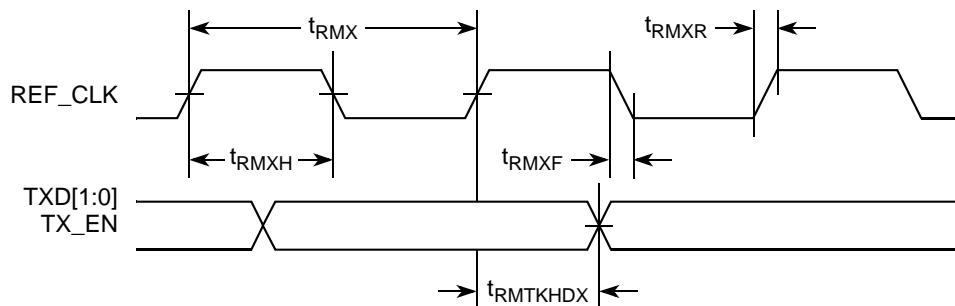
At recommended operating conditions with  $V_{DD}/OV_{DD}$  of 3.3 V  $\pm$  10%.

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit
REF_CLK clock	$t_{RMX}$	—	20	—	ns
REF_CLK duty cycle	$t_{RMXH}/t_{RMX}$	35	—	65	%
REF_CLK to RMII data TXD[1:0], TX_EN delay	$t_{RMTKHDX}$ $t_{RMTKHDX}$	2 —	—	— 10	ns
REF_CLK data clock rise time	$t_{RMXR}$	1.0	—	4.0	ns
REF_CLK data clock fall time	$t_{RMXF}$	1.0	—	4.0	ns

**Note:**

- The symbols used for timing specifications follow the pattern of  $t_{(first\ three\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$  for inputs and  $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$  for outputs. For example,  $t_{RMTKHDX}$  symbolizes RMII transmit timing (RMT) for the time  $t_{RMX}$  clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of  $t_{RMX}$  represents the RMII(RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure shows the RMII transmit AC timing diagram.



**Figure 15. RMII Transmit AC Timing Diagram**

### 8.2.3.2 RMII Receive AC Timing Specifications

This table provides the RMII receive AC timing specifications.

**Table 32. RMII Receive AC Timing Specifications**

At recommended operating conditions with  $V_{DD}/OV_{DD}$  of 3.3 V  $\pm$  10%.

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit
REF_CLK clock period	$t_{RMX}$	—	20	—	ns
REF_CLK duty cycle	$t_{RMXH}/t_{RMX}$	35	—	65	%

**Table 32. RMII Receive AC Timing Specifications (continued)**

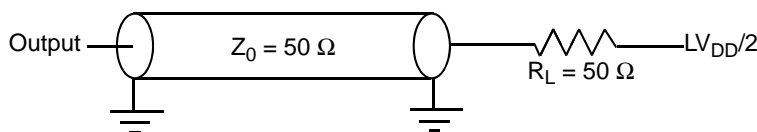
At recommended operating conditions with  $LV_{DD}/OV_{DD}$  of  $3.3\text{ V} \pm 10\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit
RXD[1:0], CRS_DV, RX_ER setup time to REF_CLK	$t_{\text{RMRDVKH}}$	4.0	—	—	ns
RXD[1:0], CRS_DV, RX_ER hold time to REF_CLK	$t_{\text{RMRDXKH}}$	2.0	—	—	ns
REF_CLK clock rise time	$t_{\text{RMXR}}$	1.0	—	4.0	ns
REF_CLK clock fall time	$t_{\text{RMXF}}$	1.0	—	4.0	ns

**Note:**

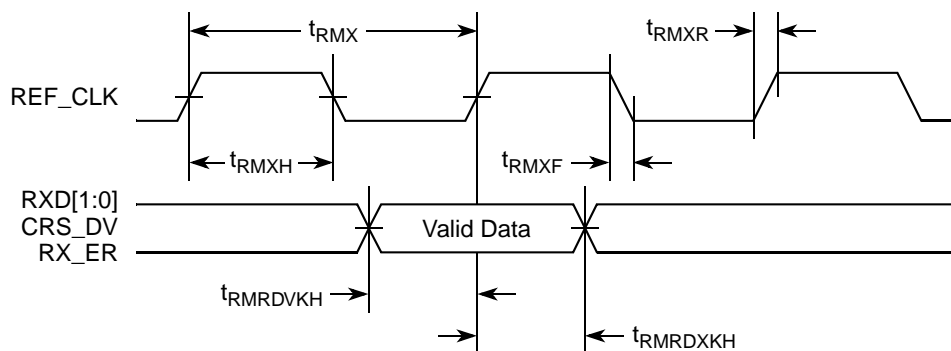
- The symbols used for timing specifications follow the pattern of  $t_{\text{(first three letters of functional block)(signal)(state)(reference)(state)}}$  for inputs and  $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$  for outputs. For example,  $t_{\text{RMRDVKH}}$  symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) reach the valid state (V) relative to the  $t_{\text{RMX}}$  clock reference (K) going to the high (H) state or setup time. Also,  $t_{\text{RMRDXKL}}$  symbolizes RMII receive timing (RMR) with respect to the time data input signals (D) went invalid (X) relative to the  $t_{\text{RMX}}$  clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of  $t_{\text{RMX}}$  represents the RMII (RM) reference (X) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

This figure provides the AC test load.



**Figure 16. AC Test Load**

This figure shows the RMII receive AC timing diagram.



**Figure 17. RMII Receive AC Timing Diagram**

## 8.2.4 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

## 8.2.4.2 TBI Receive AC Timing Specifications

This table provides the TBI receive AC timing specifications.

**Table 34. TBI Receive AC Timing Specifications**

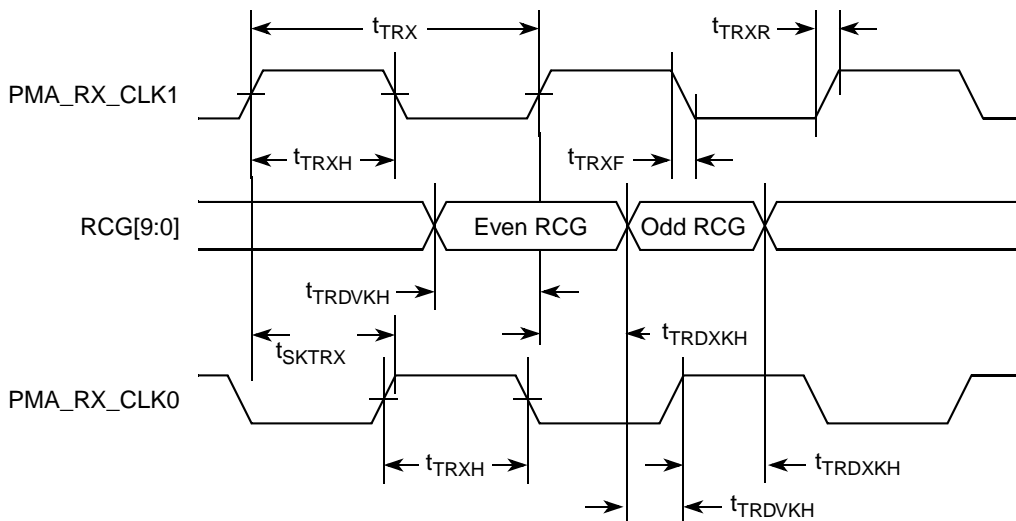
At recommended operating conditions with  $V_{DD}/OV_{DD}$  of  $3.3\text{ V} \pm 10\%$ .

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit	Notes
PMA_RX_CLK clock period	$t_{TRX}$	—	16.0	—	ns	—
PMA_RX_CLK skew	$t_{SKTRX}$	7.5	—	8.5	ns	—
RX_CLK duty cycle	$t_{TRXH}/t_{TRX}$	40	—	60	%	—
RCG[9:0] setup time to rising PMA_RX_CLK	$t_{TRDVKH}$	2.5	—	—	ns	2
RCG[9:0] hold time to rising PMA_RX_CLK	$t_{TRDXKH}$	1.0	—	—	ns	2
RX_CLK clock rise time, $V_{IL}(\text{min})$ to $V_{IH}(\text{max})$	$t_{TRXR}$	0.7	—	2.4	ns	—
RX_CLK clock fall time, $V_{IH}(\text{max})$ to $V_{IL}(\text{min})$	$t_{TRXF}$	0.7	—	2.4	ns	—

**Notes:**

- The symbols used for timing specifications follow the pattern of  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$  for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{TRDVKH}$  symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the  $t_{TRX}$  clock reference (K) going to the high (H) state or setup time. Also,  $t_{TRDXKH}$  symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the  $t_{TRX}$  clock reference (K) going to the high (H) state. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of  $t_{TRX}$  represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (TRX).
- Setup and hold time of even numbered RCG are measured from rising edge of PMA\_RX\_CLK1. Setup and hold time of odd numbered RCG are measured from rising edge of PMA\_RX\_CLK0.

This figure shows the TBI receive AC timing diagram.



**Figure 19. TBI Receive AC Timing Diagram**



## 8.2.5 RGMII and RTBI AC Timing Specifications

This table presents the RGMII and RTBI AC timing specifications.

**Table 35. RGMII and RTBI AC Timing Specifications**

At recommended operating conditions with  $V_{DD}$  of 2.5 V  $\pm$  5%.

Parameter/Condition	Symbol <sup>1</sup>	Min	Typ	Max	Unit	Notes
Data to clock output skew (at transmitter)	$t_{SKRGTKHDX}$ $t_{SKRGTKHDV}$	−0.5 —	—	— 0.5	ns	7
Data to clock input skew (at receiver)	$t_{SKRGDXKH}$ $t_{SKRGDVKH}$	1.0 —	—	— 2.6	ns	2
Clock cycle duration	$t_{RGT}$	7.2	8.0	8.8	ns	3
Duty cycle for 1000Base-T	$t_{RGTH}/t_{RGT}$	45	50	55	%	4, 5
Duty cycle for 10BASE-T and 100BASE-TX	$t_{RGTH}/t_{RGT}$	40	50	60	%	3, 5
Rise time (20–80%)	$t_{RGTR}$	—	—	0.75	ns	—
Fall time (20–80%)	$t_{RGTF}$	—	—	0.75	ns	—
GTX_CLK125 reference clock period	$t_{G125}$	—	8.0	—	ns	6
GTX_CLK125 reference clock duty cycle	$t_{G125H}/t_{G125}$	47	—	53	%	—

### Notes:

- Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of  $t_{RGT}$  represents the TBI (T) receive (Rx) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
- This implies that PC board design requires clocks to be routed such that an additional trace delay of greater than 1.5 ns can be added to the associated clock signal.
- For 10 and 100 Mbps,  $t_{RGT}$  scales to 400 ns  $\pm$  40 ns and 40 ns  $\pm$  4 ns, respectively.
- Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three  $t_{RGT}$  of the lowest speed transitioned between.
- Duty cycle reference is  $V_{DD}/2$ .
- This symbol is used to represent the external GTX\_CLK125 and does not follow the original symbol naming convention.
- In rev. 2.0 silicon, due to errata,  $t_{SKRGTKHDX}$  minimum is −2.3 ns and  $t_{SKRGTKHDV}$  maximum is 1 ns for UCC1, 1.2 ns for UCC2 option 1, and 1.8 ns for UCC2 option 2. In rev. 2.1 silicon, due to errata,  $t_{SKRGTKHDX}$  minimum is −0.65 ns for UCC2 option 1 and −0.9 for UCC2 option 2, and  $t_{SKRGTKHDV}$  maximum is 0.75 ns for UCC1 and UCC2 option 1 and 0.85 for UCC2 option 2. Refer to Errata QE\_ENET10 in *Chip Errata for the MPC8360E, Rev. 1*. UCC1 does meet  $t_{SKRGTKHDX}$  minimum for rev. 2.1 silicon.

This figure shows the RGMII and RTBI AC timing and multiplexing diagrams.

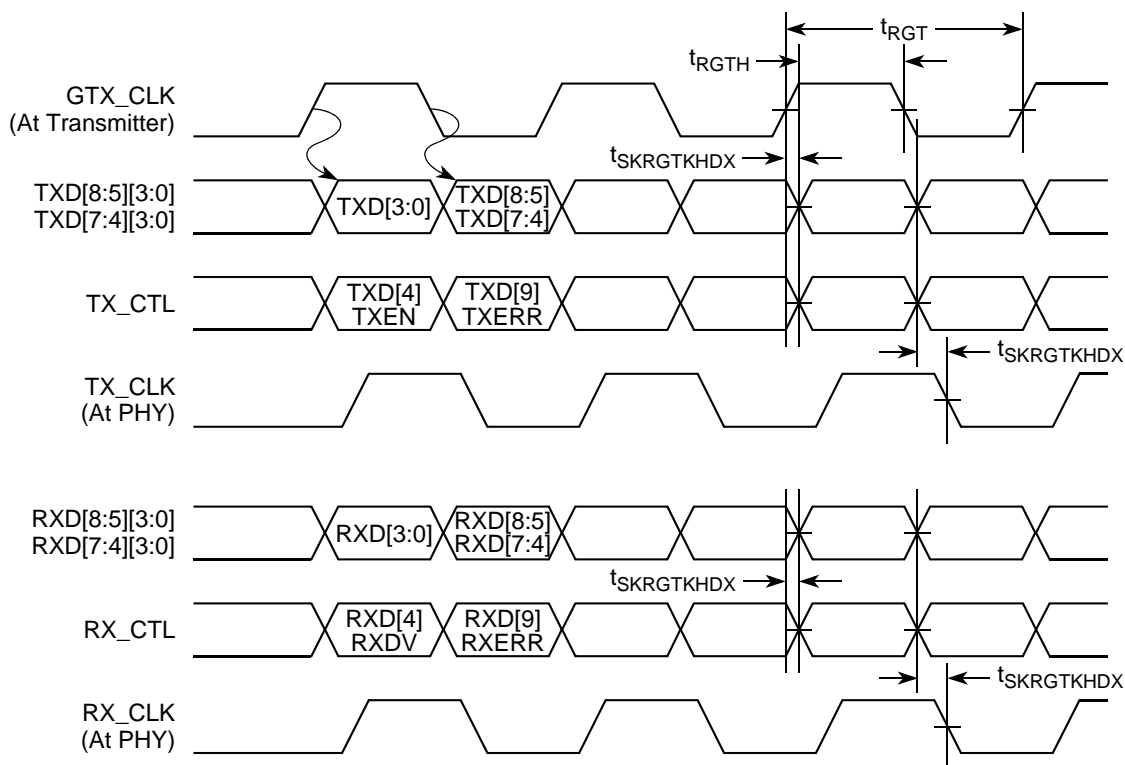


Figure 20. RGMII and RTBI AC Timing and Multiplexing Diagrams

## 8.3 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI, and RTBI are specified in [Section 8.1, “Three-Speed Ethernet Controller \(10/100/1000 Mbps\)—GMII/MII/RMII/TBI/RGMII/RTBI Electrical Characteristics.”](#)

### 8.3.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in this table.

Table 36. MII Management DC Electrical Characteristics When Powered at 3.3 V

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage (3.3 V)	$OV_{DD}$	—		2.97	3.63	V
Output high voltage	$V_{OH}$	$I_{OH} = -1.0 \text{ mA}$	$OV_{DD} = \text{Min}$	2.10	$OV_{DD} + 0.3$	V
Output low voltage	$V_{OL}$	$I_{OL} = 1.0 \text{ mA}$	$OV_{DD} = \text{Min}$	GND	0.50	V
Input high voltage	$V_{IH}$	—		2.00	—	V
Input low voltage	$V_{IL}$	—		—	0.80	V
Input current	$I_{IN}$	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$		—	$\pm 10$	$\mu\text{A}$

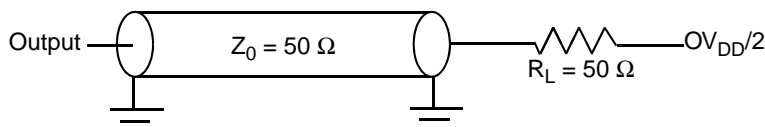
**Table 41. Local Bus General Timing Parameters—DLL Bypass Mode<sup>9</sup> (continued)**

Parameter	Symbol <sup>1</sup>	Min	Max	Unit	Notes
Local bus clock to output valid	$t_{LBKHOV}$	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	$t_{LBKHOZ}$	—	4	ns	8

**Notes:**

1. The symbols used for timing specifications follow the pattern of  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$  for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{LBIXKH1}$  symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the  $t_{LBK}$  clock reference (K) goes high (H), in this case for clock one (1). Also,  $t_{LBKHOX}$  symbolizes local bus timing (LB) for the  $t_{LBK}$  clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for  $\overline{LGTA}$  and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from  $OV_{DD}/2$  of the rising/falling edge of LCLK0 to  $0.4 \times OV_{DD}$  of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5.  $t_{LBOTOT1}$  should be used when RCWH[LALE] is not set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
6.  $t_{LBOTOT2}$  should be used when RCWH[LALE] is set and when the load on LALE output pin is at least 10 pF less than the load on LAD output pins.
7.  $t_{LBOTOT3}$  should be used when RCWH[LALE] is set and when the load on LALE output pin equals to the load on LAD output pins.
8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

This figure provides the AC test load for the local bus.


**Figure 22. Local Bus C Test Load**

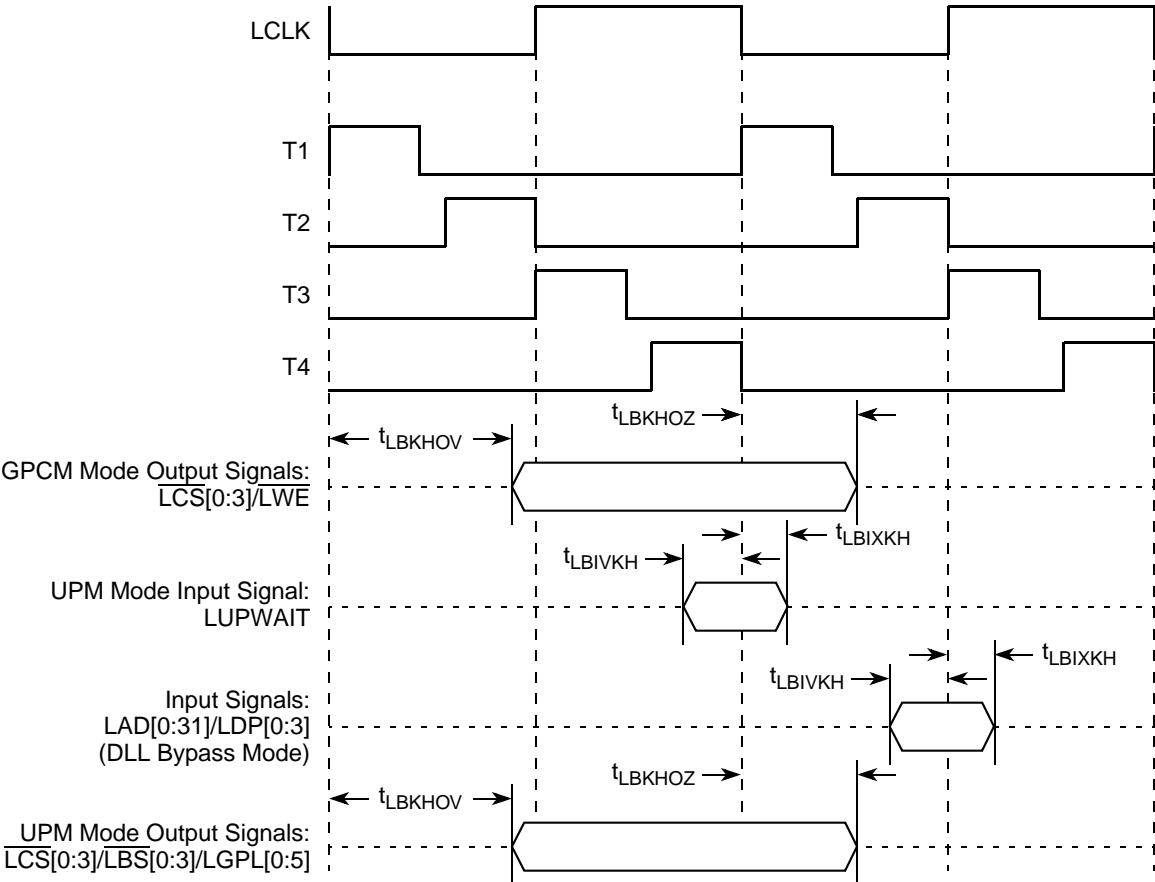


Figure 27. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 (DLL Bypass Mode)

## 11.2 I<sup>2</sup>C AC Electrical Specifications

This table provides the AC timing parameters for the I<sup>2</sup>C interface of the device.

**Table 45. I<sup>2</sup>C AC Electrical Specifications**

All values refer to  $V_{IH}$  (min) and  $V_{IL}$  (max) levels (see Table 44).

Parameter	Symbol <sup>1</sup>	Min	Max	Unit	Note
SCL clock frequency	$f_{I2C}$	0	400	kHz	2
Low period of the SCL clock	$t_{I2CL}$	1.3	—	μs	—
High period of the SCL clock	$t_{I2CH}$	0.6	—	μs	—
Setup time for a repeated START condition	$t_{I2SVKH}$	0.6	—	μs	—
Hold time (repeated) START condition (after this period, the first clock pulse is generated)	$t_{I2SXKL}$	0.6	—	μs	—
Data setup time	$t_{I2DVKH}$	100	—	ns	3
Data hold time: CBUS compatible masters I <sup>2</sup> C bus devices	$t_{I2DXKL}$	— 0 <sup>2</sup>	— 0.9 <sup>3</sup>	μs	—
Rise time of both SDA and SCL signals	$t_{I2CR}$	$20 + 0.1 C_B^4$	300	ns	—
Fall time of both SDA and SCL signals	$t_{I2CF}$	$20 + 0.1 C_B^4$	300	ns	—
Set-up time for STOP condition	$t_{I2PVKH}$	0.6	—	μs	—
Bus free time between a STOP and START condition	$t_{I2KHDX}$	1.3	—	μs	—
Noise margin at the LOW level for each connected device (including hysteresis)	$V_{NL}$	$0.1 \times OV_{DD}$	—	V	—
Noise margin at the HIGH level for each connected device (including hysteresis)	$V_{NH}$	$0.2 \times OV_{DD}$	—	V	—

### Notes:

- The symbols used for timing specifications follow the pattern of  $t_{(first\ two\ letters\ of\ functional\ block)(signal)(state)(reference)(state)}$  for inputs and  $t_{(first\ two\ letters\ of\ functional\ block)(reference)(state)(signal)(state)}$  for outputs. For example,  $t_{I2DVKH}$  symbolizes I<sup>2</sup>C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the  $t_{I2C}$  clock reference (K) going to the high (H) state or setup time. Also,  $t_{I2SXKL}$  symbolizes I<sup>2</sup>C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the  $t_{I2C}$  clock reference (K) going to the low (L) state or hold time. Also,  $t_{I2PVKH}$  symbolizes I<sup>2</sup>C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the  $t_{I2C}$  clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
- The device provides a hold time of at least 300 ns for the SDA signal (referred to the  $V_{IH}$  min of the SCL signal) to bridge the undefined region of the falling edge of SCL.
- The maximum  $t_{I2DVKH}$  has only to be met if the device does not stretch the LOW period ( $t_{I2CL}$ ) of the SCL signal.
- $C_B$  = capacitance of one bus line in pF.

## 14.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

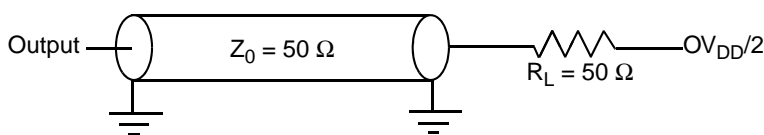
**Table 52. GPIO Input AC Timing Specifications<sup>1</sup>**

Characteristic	Symbol <sup>2</sup>	Typ	Unit
GPIO inputs—minimum pulse width	$t_{PIWD}$	20	ns

**Notes:**

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of CLKIN. Timings are measured at the pin.
2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least  $t_{PIWD}$  ns to ensure proper operation.

This figure provides the AC test load for the GPIO.



**Figure 40. GPIO AC Test Load**

## 15 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8360E/58E.

### 15.1 IPIC DC Electrical Characteristics

This table provides the DC electrical characteristics for the external interrupt pins of the IPIC.

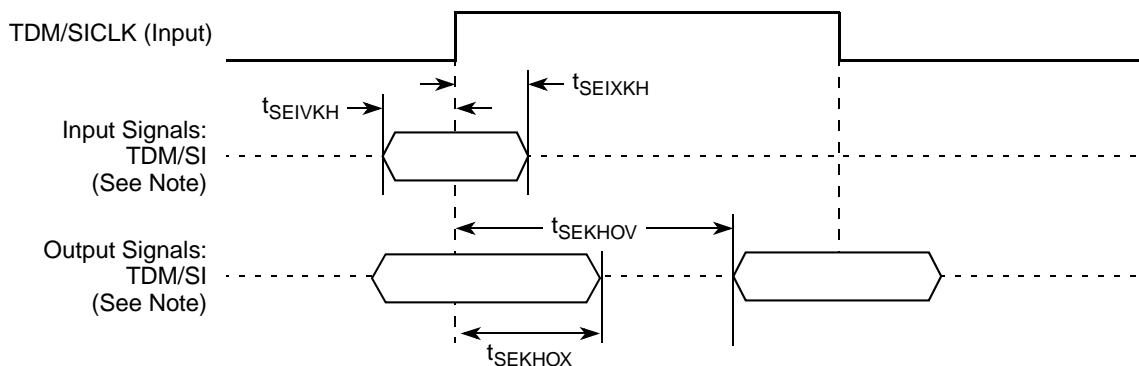
**Table 53. IPIC DC Electrical Characteristics**

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	$V_{IH}$	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	$V_{IL}$	—	-0.3	0.8	V
Input current	$I_{IN}$	—	—	$\pm 10$	$\mu A$
Output low voltage	$V_{OL}$	$I_{OL} = 6.0 \text{ mA}$	—	0.5	V
Output low voltage	$V_{OL}$	$I_{OL} = 3.2 \text{ mA}$	—	0.4	V

**Notes:**

1. This table applies for pins  $\overline{IRQ}[0:7]$ ,  $\overline{IRQ\_OUT}$ ,  $\overline{MCP\_OUT}$ , and CE ports Interrupts.
2.  $\overline{IRQ\_OUT}$  and  $\overline{MCP\_OUT}$  are open drain pins, thus  $V_{OH}$  is not relevant for those pins.

This figure shows the TDM/SI timing with external clock.



**Note:** The clock edge is selectable on TDM/SI

**Figure 45. TDM/SI AC Timing (External Clock) Diagram**

## 17.3 UTOPIA/POS

This section describes the DC and AC electrical specifications for the UTOPIA/POS of the MPC8360E/58E.

## 17.4 UTOPIA/POS DC Electrical Characteristics

This table provides the DC electrical characteristics for the device UTOPIA.

**Table 59. UTOPIA DC Electrical Characteristics**

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	$V_{OH}$	$I_{OH} = -8.0 \text{ mA}$	2.4	—	V
Output low voltage	$V_{OL}$	$I_{OL} = 8.0 \text{ mA}$	—	0.5	V
Input high voltage	$V_{IH}$	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	$V_{IL}$	—	-0.3	0.8	V
Input current	$I_{IN}$	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	$\pm 10$	$\mu\text{A}$

## 17.5 UTOPIA/POS AC Timing Specifications

This table provides the UTOPIA input and output AC timing specifications.

**Table 60. UTOPIA AC Timing Specifications<sup>1</sup>**

Characteristic	Symbol <sup>2</sup>	Min	Max	Unit	Notes
UTOPIA outputs—Internal clock delay	$t_{UIKHOV}$	0	11.5	ns	—
UTOPIA outputs—External clock delay	$t_{UEKHOV}$	1	11.6	ns	—
UTOPIA outputs—Internal clock high impedance	$t_{UIKHOX}$	0	8.0	ns	—
UTOPIA outputs—External clock high impedance	$t_{UEKHOX}$	1	10.0	ns	—
UTOPIA inputs—Internal clock input setup time	$t_{UIIVKH}$	6	—	ns	—
UTOPIA inputs—External clock input setup time	$t_{UEIVKH}$	4	—	ns	3

This figure shows the UTOPIA timing with internal clock.

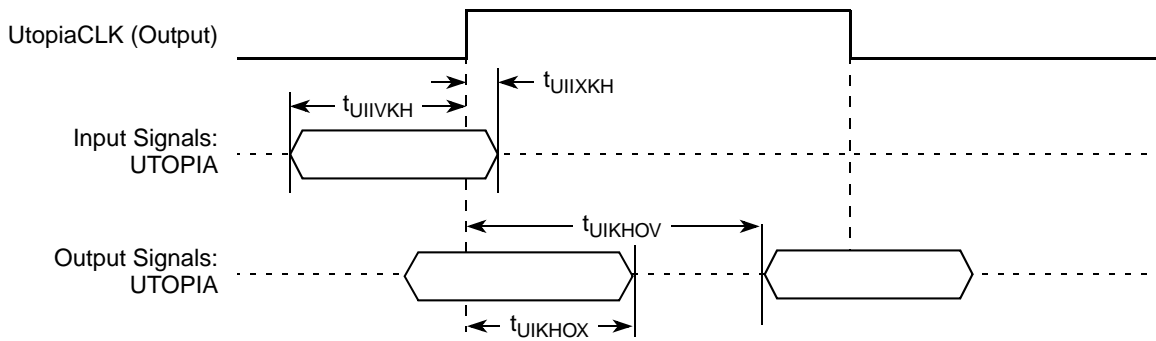


Figure 48. UTOPIA AC Timing (Internal Clock) Diagram

## 18 HDLC, BISYNC, Transparent, and Synchronous UART

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), BISYNC, transparent, and synchronous UART protocols of the MPC8360E/58E.

### 18.1 HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

This table provides the DC electrical characteristics for the device HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 61. HDLC, BISYNC, Transparent, and Synchronous UART DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	$V_{OH}$	$I_{OH} = -2.0 \text{ mA}$	2.4	—	V
Output low voltage	$V_{OL}$	$I_{OL} = 3.2 \text{ mA}$	—	0.5	V
Input high voltage	$V_{IH}$	—	2.0	$OV_{DD} + 0.3$	V
Input low voltage	$V_{IL}$	—	-0.3	0.8	V
Input current	$I_{IN}$	$0 \text{ V} \leq V_{IN} \leq OV_{DD}$	—	$\pm 10$	$\mu\text{A}$

### 18.2 HDLC, BISYNC, Transparent, and Synchronous UART AC Timing Specifications

These tables provide the input and output AC timing specifications for HDLC, BISYNC, transparent, and synchronous UART protocols.

Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications<sup>1</sup>

Characteristic	Symbol <sup>2</sup>	Min	Max	Unit
Outputs—Internal clock delay	$t_{HIKHOV}$	0	11.2	ns
Outputs—External clock delay	$t_{HEKHOV}$	1	10.8	ns



**Table 62. HDLC, BISYNC, and Transparent AC Timing Specifications<sup>1</sup> (continued)**

Characteristic	Symbol <sup>2</sup>	Min	Max	Unit
Outputs—Internal clock high impedance	$t_{HIKHOX}$	-0.5	5.5	ns
Outputs—External clock high impedance	$t_{HEKHOX}$	1	8	ns
Inputs—Internal clock input setup time	$t_{HIIVKH}$	8.5	—	ns
Inputs—External clock input setup time	$t_{HEIVKH}$	4	—	ns
Inputs—Internal clock input hold time	$t_{HIIXKH}$	1.4	—	ns
Inputs—External clock input hold time	$t_{HEIXKH}$	1	—	ns

**Notes:**

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$  for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{HIKHOX}$  symbolizes the outputs internal timing (HI) for the time  $t_{\text{serial}}$  memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

**Table 63. Synchronous UART AC Timing Specifications<sup>1</sup>**

Characteristic	Symbol <sup>2</sup>	Min	Max	Unit
Outputs—Internal clock delay	$t_{UAIKHOV}$	0	11.3	ns
Outputs—External clock delay	$t_{UAEKHOV}$	1	14	ns
Outputs—Internal clock high impedance	$t_{UAIKHOX}$	0	11	ns
Outputs—External clock high impedance	$t_{UAEKHOX}$	1	14	ns
Inputs—Internal clock input setup time	$t_{UAIIVKH}$	6	—	ns
Inputs—External clock input setup time	$t_{UAEIVKH}$	8	—	ns
Inputs—Internal clock input hold time	$t_{UAIIXKH}$	1	—	ns
Inputs—External clock input hold time	$t_{UAEIXKH}$	1	—	ns

**Notes:**

- Output specifications are measured from the 50% level of the rising edge of CLKIN to the 50% level of the signal. Timings are measured at the pin.
- The symbols used for timing specifications follow the pattern of  $t_{(\text{first two letters of functional block})(\text{signal})(\text{state})(\text{reference})(\text{state})}$  for inputs and  $t_{(\text{first two letters of functional block})(\text{reference})(\text{state})(\text{signal})(\text{state})}$  for outputs. For example,  $t_{HIKHOX}$  symbolizes the outputs internal timing (HI) for the time  $t_{\text{serial}}$  memory clock reference (K) goes from the high state (H) until outputs (O) are invalid (X).

This figure provides the AC test load.

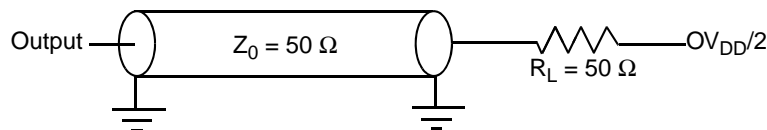

**Figure 49. AC Test Load**

Table 67. MPC8358E TBGA Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
LV <sub>DD1</sub>	C17, D16	Power for UCC2 Ethernet interface option 1 (2.5 V, 3.3 V)	LV <sub>DD1</sub>	9
LV <sub>DD2</sub>	B18, E21	Power for UCC2 Ethernet interface option 2 (2.5 V, 3.3 V)	LV <sub>DD2</sub>	9
V <sub>DD</sub>	C36, D29, D35, E16, F9, F12, F15, F17, F18, F20, F21, F23, F25, F26, F29, F31, F32, F33, G6, J6, K32, M32, N6, P33, R6, R32, U32, V6, Y5, Y32, AB6, AB33, AD6, AF32, AK6, AL6, AM7, AM9, AM10, AM11, AM12, AM13, AM14, AM15, AM18, AM21, AM25, AM28, AM32, AN15, AN21, AN26, AU9, AU17	Power for core (1.2 V)	V <sub>DD</sub>	—
OV <sub>DD</sub>	A10, B9, B15, B32, C1, C12, C22, C29, D24, E3, E10, E27, G4, H35, J1, J35, K2, M4, N3, N34, R2, R37, T36, U2, U33, V4, V34, W3, Y35, Y37, AA1, AA36, AB2, AB34	PCI, 10/100 Ethernet, and other standard (3.3 V)	OV <sub>DD</sub>	—
MVREF1	AN20	I	DDR reference voltage	—
MVREF2	AU32	I	DDR reference voltage	—
SPARE1	B11	I/O	OV <sub>DD</sub>	8
SPARE3	AH32	—	GV <sub>DD</sub>	8
SPARE4	AU18	—	GV <sub>DD</sub>	7
SPARE5	AP1	—	GV <sub>DD</sub>	8

# 21 Clocking

This figure shows the internal distribution of clocks within the MPC8360E.

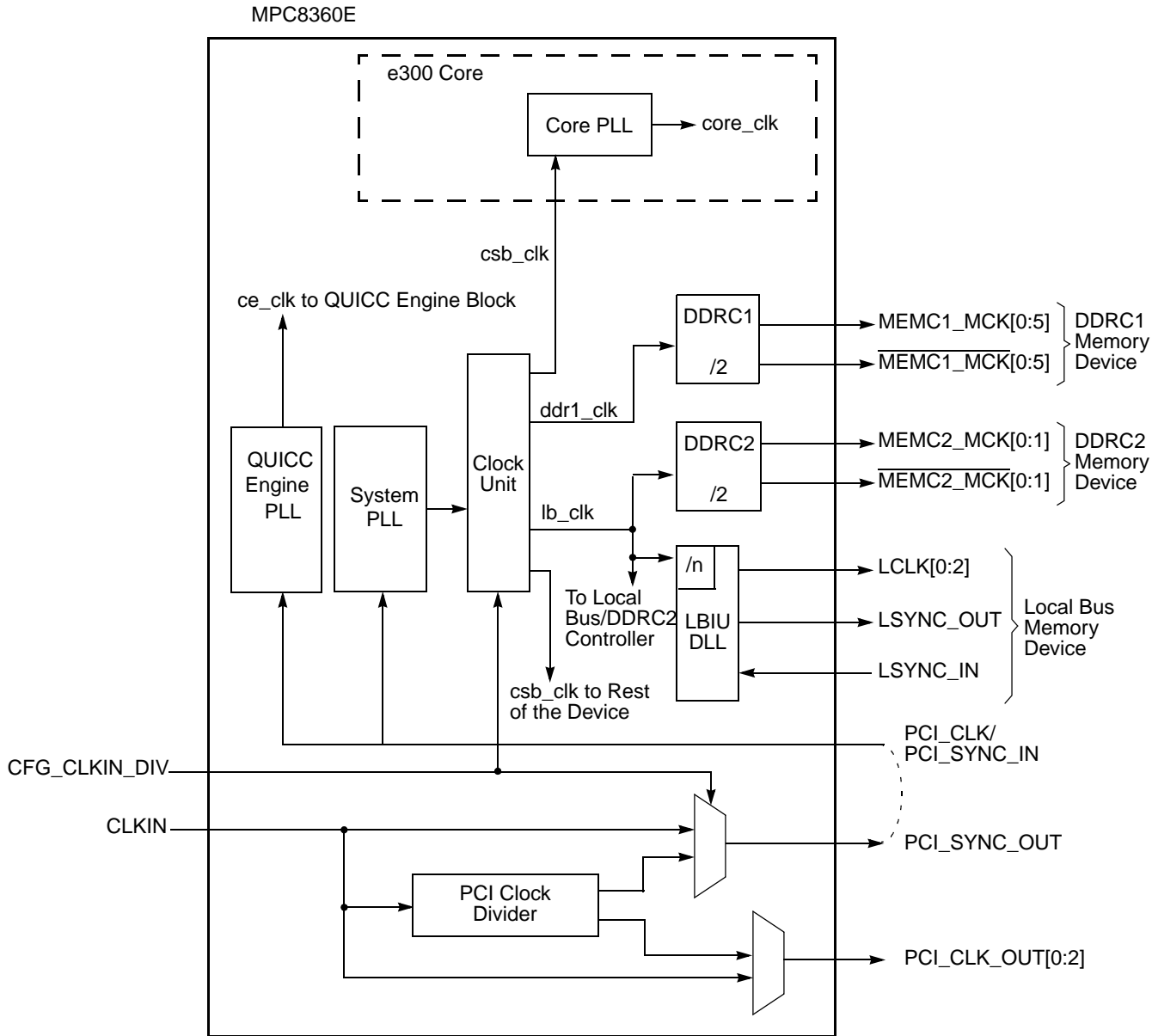
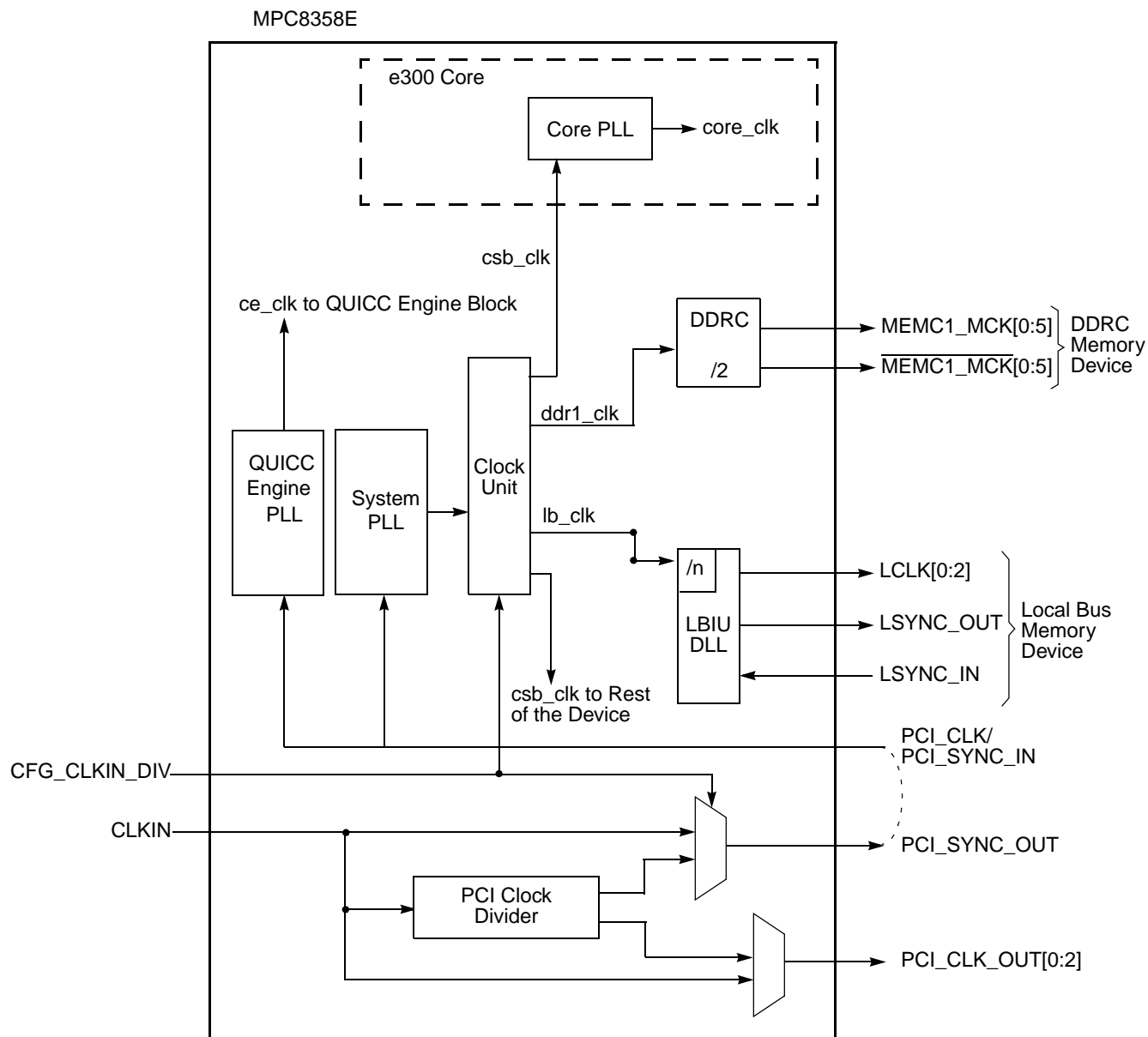


Figure 54. MPC8360E Clock Subsystem

This figure shows the internal distribution of clocks within the MPC8358E.



**Figure 55. MPC8358E Clock Subsystem**

The primary clock source for the device can be one of two inputs, CLKIN or PCI\_CLK, depending on whether the device is configured in PCI host or PCI agent mode. Note that in PCI host mode, the primary clock input also depends on whether PCI clock outputs are selected with RCWH[PCICKDRV]. When the device is configured as a PCI host device (RCWH[PCIHOST] = 1) and PCI clock output is selected (RCWH[PCICKDRV] = 1), CLKIN is its primary input clock. CLKIN feeds the PCI clock divider (+2) and the multiplexors for PCI\_SYNC\_OUT and PCI\_CLK\_OUT. The CFG\_CLKIN\_DIV configuration input selects whether CLKIN or CLKIN/2 is driven out on the PCI\_SYNC\_OUT signal. The OCCR[PCIOEN $n$ ] parameters enable the PCI\_CLK\_OUT $n$ , respectively.

PCI\_SYNC\_OUT is connected externally to PCI\_SYNC\_IN to allow the internal clock subsystem to synchronize to the system PCI clocks. PCI\_SYNC\_OUT must be connected properly to PCI\_SYNC\_IN, with equal delay to all PCI agent devices in the system, to allow the device to function. When the device is configured as a PCI agent device, PCI\_CLK is the primary input

## 22.3.1 Experimental Determination of the Junction Temperature with a Heat Sink

When heat sink is used, the junction temperature is determined from a thermocouple inserted at the interface between the case of the package and the interface material. A clearance slot or hole is normally required in the heat sink. Minimizing the size of the clearance is important to minimize the change in thermal performance caused by removing part of the thermal interface to the heat sink. Because of the experimental difficulties with this technique, many engineers measure the heat sink temperature and then back calculate the case temperature using a separate measurement of the thermal resistance of the interface. From this case temperature, the junction temperature is determined from the junction-to-case thermal resistance.

$$T_J = T_C + (R_{\theta JC} \times P_D)$$

where:

$T_J$  = junction temperature (°C)

$T_C$  = case temperature of the package (°C)

$R_{\theta JC}$  = junction to case thermal resistance (°C/W)

$P_D$  = power dissipation (W)

## 23 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8360E/58E. Additional information can be found in *MPC8360E/MPC8358E PowerQUICC Design Checklist* (AN3097).

### 23.1 System Clocking

The device includes two PLLs, as follows.

- The platform PLL (AV<sub>DD1</sub>) generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in [Section 21.1, “System PLL Configuration.”](#)
- The e300 core PLL (AV<sub>DD2</sub>) generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in [Section 21.2, “Core PLL Configuration.”](#)

### 23.2 PLL Power Supply Filtering

Each of the PLLs listed above is provided with power through independent power supply pins (AV<sub>DD1</sub>, AV<sub>DD2</sub>, respectively). The AV<sub>DD</sub> level should always be equivalent to V<sub>DD</sub>, and preferably these voltages are derived directly from V<sub>DD</sub> through a low frequency filter scheme such as the following.

There are a number of ways to reliably provide power to the PLLs, but the recommended solution is to provide five independent filter circuits as illustrated in [Figure 56](#), one to each of the five AV<sub>DD</sub> pins. By providing independent filters to each PLL, the opportunity to cause noise injection from one PLL to the other is reduced.

This circuit is intended to filter noise in the PLLs resonant frequency range from a 500 kHz to 10 MHz range. It should be built with surface mount capacitors with minimum Effective Series Inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

Each circuit should be placed as close as possible to the specific AV<sub>DD</sub> pin being supplied to minimize noise coupled from nearby circuits. It should be possible to route directly from the capacitors to the AV<sub>DD</sub> pin, which is on the periphery of package, without the inductance of vias.